(11)

EP 0 776 032 A3

(12)

EUROPEAN PATENT APPLICATION

(88) Date of publication A3: 15.04.1998 Bulletin 1998/16 (51) Int. Cl.6: H01L 21/311

(43) Date of publication A2: 28.05.1997 Bulletin 1997/22

(21) Application number: 96117162.6

(22) Date of filing: 25.10.1996

(84) Designated Contracting States: DE FR GB NL

(30) Priority: 26.10.1995 JP 302139/95

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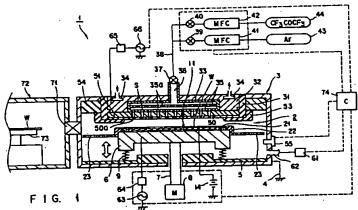
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Plasma etching method (54)

A contact hole is formed in an SiO_2 film on a sil-(57)icon wafer (W) by a plasma etching, using a photoresist as a mask. A process gas is a mixture of an etching gas of HFPO and a carrier gas of Ar at a volume ratio of from 1:17.5 to 1:20. The process gas is fed into a process chamber (3) which houses the silicon water and is set at a pressure of from 10 mTorr to 100 mTorr. The process gas is turned into plasma by electric discharge, and the SiO₂ film is subjected to etching with the plasma. During the etching, the target surface of the wafer is kept at a temperature of from 50°C to 100°C. The etching gas of

HFPO is represented by a structural formula as follows:





EUROPEAN SEARCH REPORT

Application Number EP 96 11 7162

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Application Number

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CLAIMS INCURRING FEES	-
The present European patent application comprised at the time of filing more than ten claims.	
Only part of the claims have been paid within the prescribed time limit. The present European search report has been drawn up for the first ten claims and for those claims for which claims fees have been paid, namely claim(s):	
No claims fees have been paid within the prescribed time limit. The present European search report has been drawn up for the first ten claims.	28
LACK OF UNITY OF INVENTION	
The Search Division considers that the present European patent application does not comply with the requirements of unity of invention and relates to several inventions or groups of inventions, namely:	
SEE SHEET B	
(In case of Lack of Unity)	
All further search fees have been paid within the fixed time limit. The present European search report been drawn up for all claims.	:has
Only part of the further search fees have been paid within the fixed time limit. The present European search report has been drawn up for those parts of the European patent application which relate to the search respect of which search fees have been paid, namely claims:	10
None of the further search fees have been paid within the fixed time limit. The present European search report has been drawn up for those parts of the European patent application which relate to the investirst mentioned in the claims, namely claims:	irch ation



LACK OF UNITY OF INVENTION SHEET B

Application Number

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The Search Division considers that the present European patent application does not comply with the requirements of unity of invention and relates to several inventions or groups of inventions, namely:

1. Claim: 1 to 10 (searched)

A process gas including hexafluoropropene oxide and a process for etching silicon oxide using said gas.

2. Claim : 11 to 20 (searched)

A process gas including hexafluoroacetone and a process for etching silicon oxide using said gas.